

BLUE LINE™ Hyper-Bright LED Hyper 3 mm (T1) LED, Non Diffused

The Leader in Silicon Carbide Solid State Technology

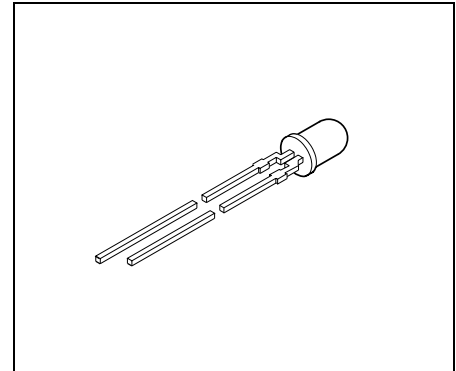
Applications

- Full Color Displays & Moving Message Signs
- Solid State Incandescent Replacement Bulbs
- High Ambient Panel Indicators
- Color Printers & Scanners
- Medical & Analytical Instruments

Features

- colorless, clear package
- optical coupling into light pipes
- for use as optical indicator
- solder leads with stand-off
- available taped on reel
- ESD withstand voltage of 2 kV according to MIL STD 883D, Method 3015.7

G-SiC® Technology
Super Blue LED
C430-CB290-E1200



Kesun's Super blue LEDs are a new generation of solid-state blue LED emitters which combine highly efficient GaN with Cree's proprietary SiC substrate to deliver the ultimate price/performance for high intensity blue LEDs. The C430-CB290-E1200 is designed for use in high ambient light conditions with a typical output of 1150 μ W and a 430 nm peak wavelength (at 20 mA).

Type Topside View	Color of Emission	Color of the Light Emitting Area	Luminous Intensity $I_F = 10$ mA I_V (mcd)	Ordering Code
KS 3430-L KS 3430-M KS 3430-N KS 3430-P KS 3430-Q	blue	colorless clear	16 ... 32 25 ... 50 40 ... 80 63 ... 125	K62703-Q4068

Luminous intensity ratio in one packaging unit $I_{V \max} / I_{V \min} \leq 2.0$.

Luminous intensity is specified at a current pulse duration of 25 ms.

Maximum Ratings

Parameter	Symbol	Values	Unit
Operating temperature range	T_{op}	- 40 ... + 100	°C
Storage temperature range	T_{stg}	- 40 ... + 100	°C
Junction temperature	T_j	+ 100	°C
Forward current	I_F	20	mA
Reverse voltage ¹⁾	V_R	5	V
Power dissipation $T_A \leq 25^\circ\text{C}$	P_{tot}	100	mW
Thermal resistance Junction / air mounted on PC board*) (pad size $\geq 16\text{ mm}^2$)	$R_{th JA}$	500	K/W

Maximum Ratings at $T_A = 25^\circ\text{C}$ Notes 1&3

C430-CB290-E1200

DC Forward Current	30 mA
Peak Forward Current (1/10 duty cycle @ 1kHz)	70 mA
LED Junction Temperature	125°C
Reverse Voltage	5 V
Operating Temperature Range	-20°C to +80°C
Storage Temperature Range	-30°C to +100°C
Electrostatic Discharge Threshold (HBM) Note 2	1200 V

Electrical/Optical Characteristics at $T_A = 25^\circ\text{C}$ Note 3

If = 20 mA

C430-CB290-E1200

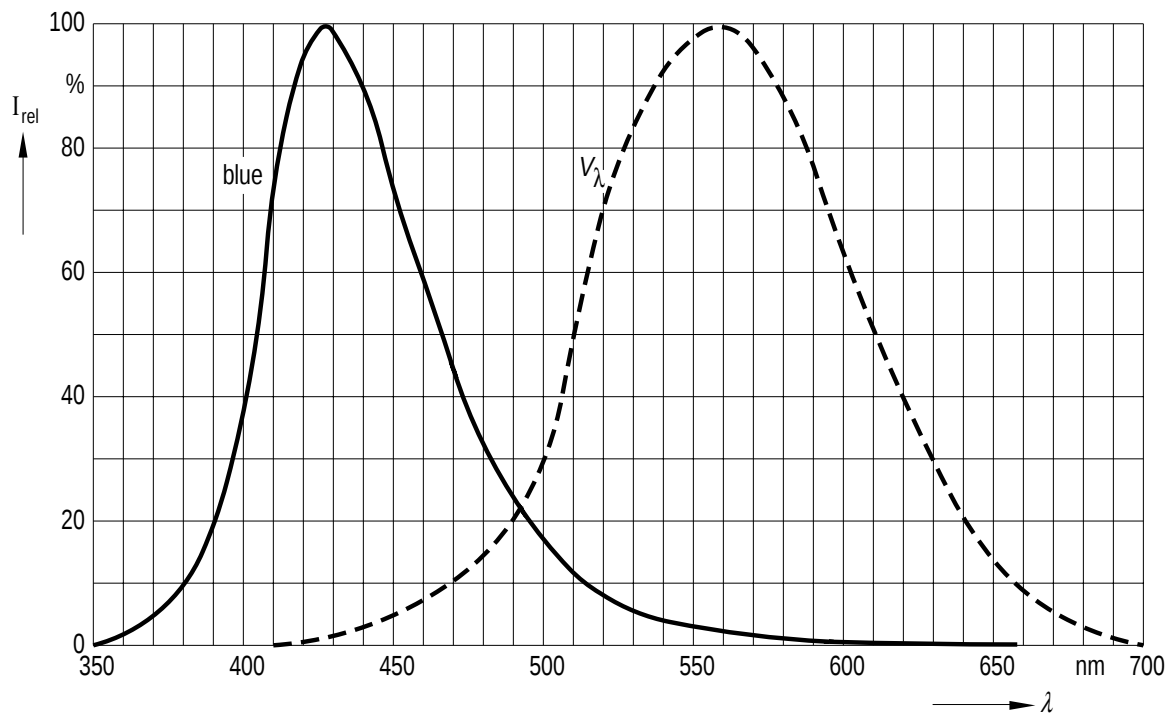
Symbol (units)	Description	Min.	Typ.	Max.
V_f (V)	Forward Voltage	—	3.8	4.5
P (μW)	Radiant Flux	850	1150	—
I (μA)	Reverse Current ($V_R = 5\text{V}$)	—	—	10
I_v (mcd)	Chip Luminous Intensity	—	6.0	—
λ_p (nm)	Peak Wavelength	426	428	430
λ_d (nm)	Dominant Wavelength	464	466	468
$\lambda\Delta$ (nm)	Halfwidth	—	65	—
τ (ns)	Optical Rise Time	—	30	—

Characteristics ($T_A = 25\text{ }^{\circ}\text{C}$)

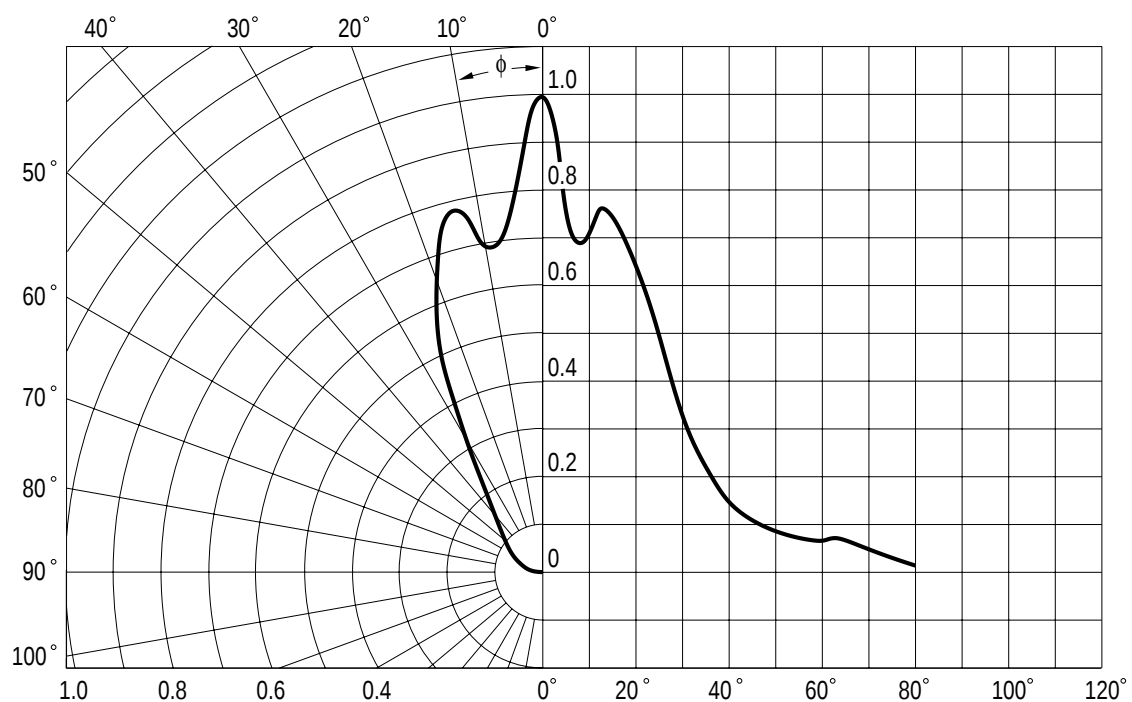
Parameter	Symbol	Values		Unit
		typ.	max.	
Wavelength at peak emission $I_F = 10\text{ mA}$	λ_{peak}	428	—	nm
Dominant wavelength $I_F = 10\text{ mA}$	λ_{dom}	466	—	nm
Spectral bandwidth at 50% $I_{\text{rel max}}$ $I_F = 10\text{ mA}$	$\Delta\lambda$	60	—	nm
Viewing angle at 50% I_v (Vollwinkel)	2ϕ	50	—	Grad deg.
Forward voltage $I_F = 10\text{ mA}$	V_F	3.5	4.2	V
Reverse current $V_R = 5\text{ V}$	I_R	0.01	10	μA
Temperature coefficient of λ_{dom} ($I_F = 10\text{ mA}$)	TC_{λ}	0.03	—	nm/K
Temperature coefficient of λ_{peak} ($I_F = 10\text{ mA}$)	TC_{λ}	0.004	—	nm/K
Temperature coefficient of V_F ($I_F = 10\text{ mA}$)	TC_V	— 3.1	—	mV/K

Relative spectral emission $I_{rel} = f(\lambda)$, $T_A = 25\text{ }^{\circ}\text{C}$, $I_F = 10\text{ mA}$

$V(\lambda) =$ Standard eye response curve

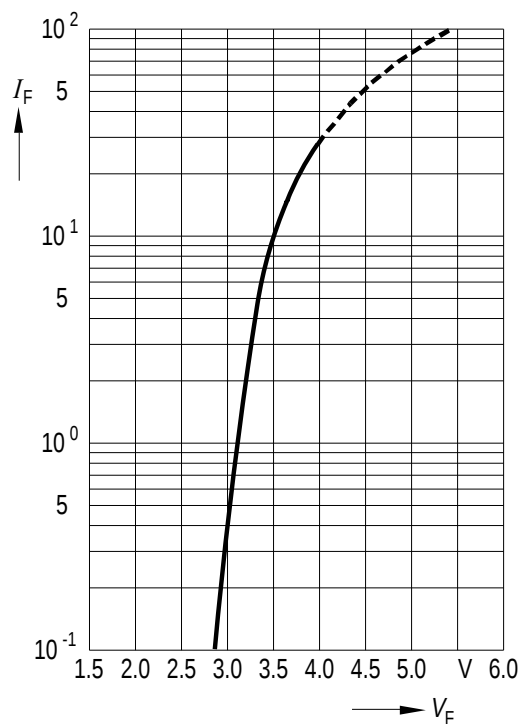


Radiation characteristic $I_{rel} = f(\phi)$



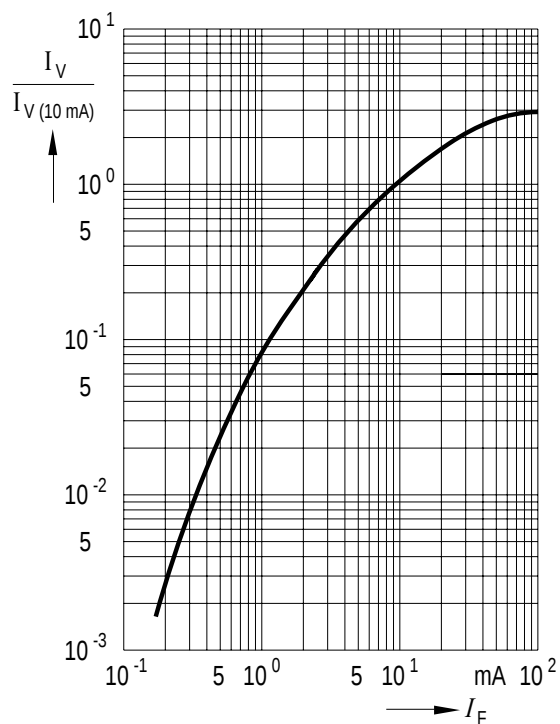
Forward current $I_F = f(V_F)$

$T_A = 25\text{ }^{\circ}\text{C}$



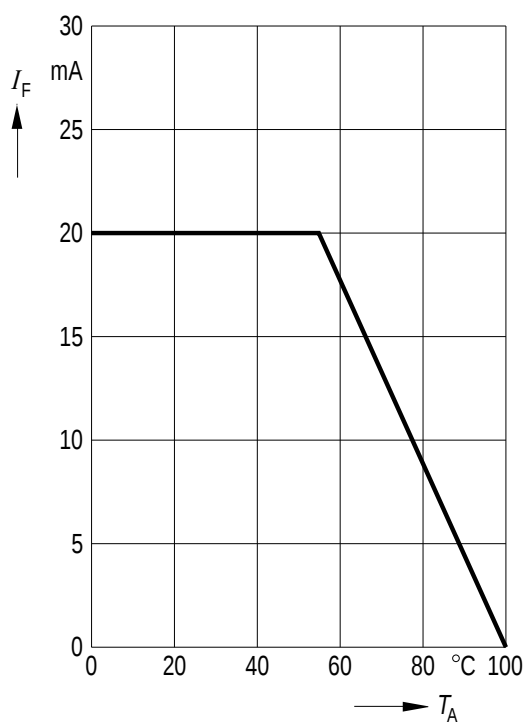
Relative luminous intensity $I_V/I_{V(10\text{ mA})} = f(I_F)$

$T_A = 25\text{ }^{\circ}\text{C}$



Max. permissible forward current

$I_F = f(T_A)$



Relative luminous intensity $I_V/I_{V(25\text{ }^{\circ}\text{C})} = f(T_A)$

$I_F = 10\text{ mA}$

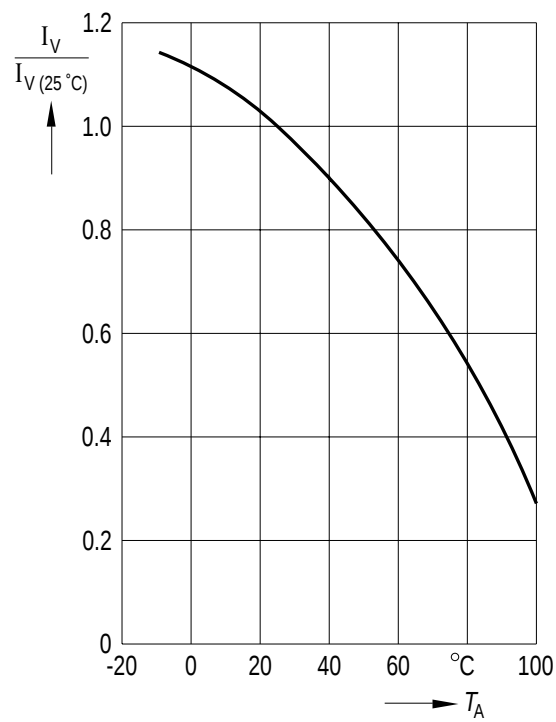


Fig. 1 Forward Voltage vs. Forward Current

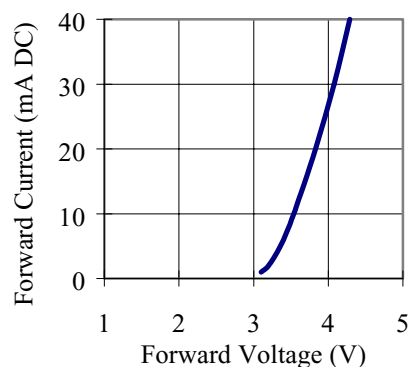


Fig. 2 Relative Intensity vs. Wavelength

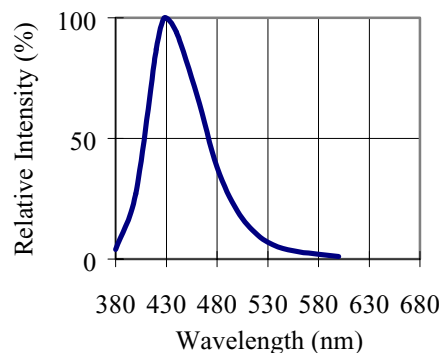


Fig. 3 Relative Intensity vs. Forward Current

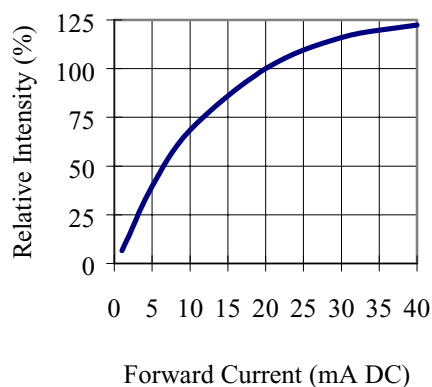


Fig. 4 Relative Intensity vs. Lead Temperature (Pulsed 20 mA; 300μs pulse, 10ms period)

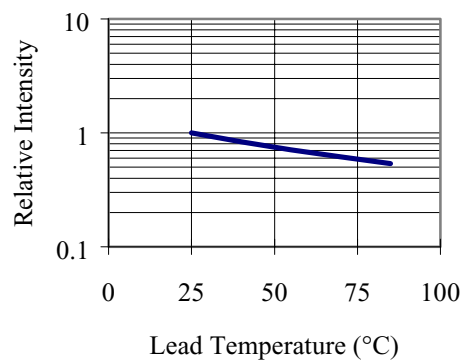


Fig. 5 Forward Current vs. Ambient Temperature

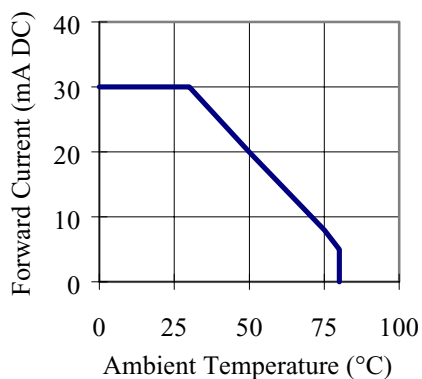
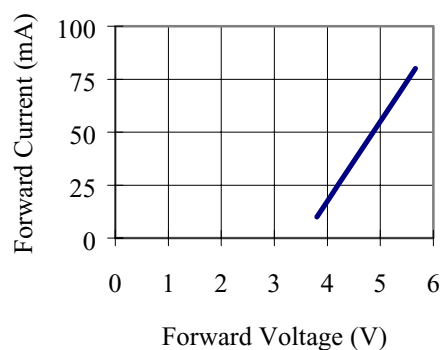
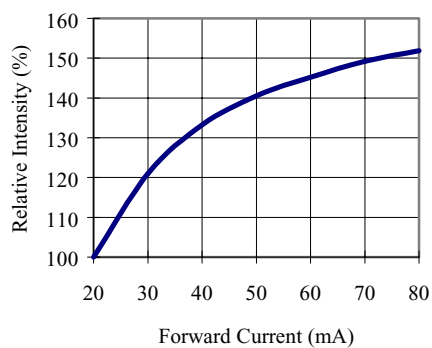


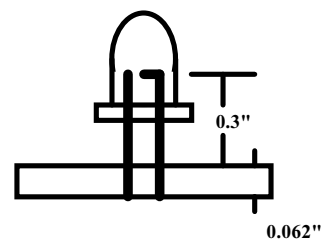
Fig. 6 Peak Forward Voltage vs. Forward Current (100μs test pulse, 1% duty cycle)



**Fig. 7 Relative Intensity vs. Peak Forward Current
(300 μ s pulse width; 10ms period)**

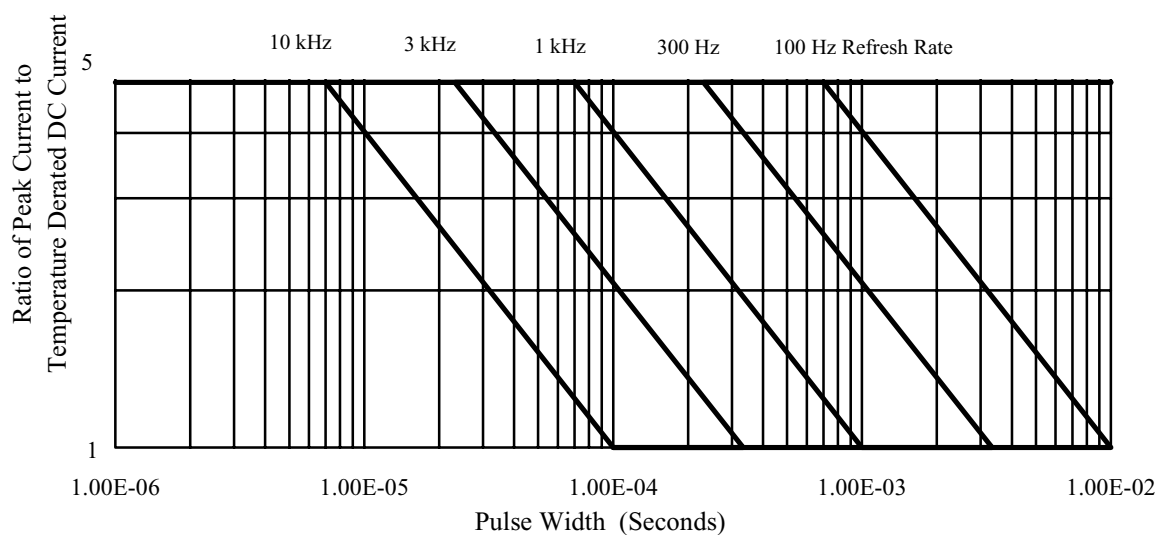


**Fig. 8 LED Mounting Conditions Used To
Generate The Pulse Derating Curve**

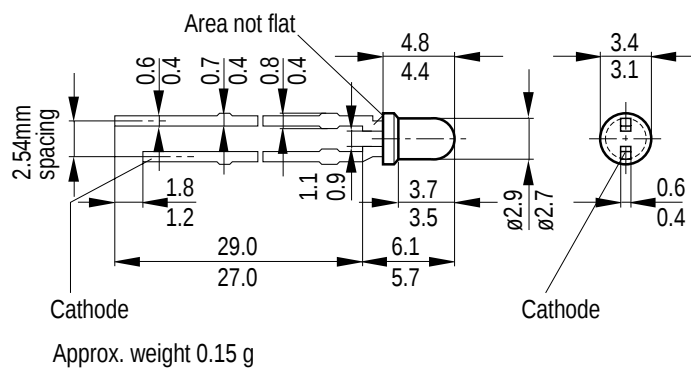


The LED was mounted on a 1/16" phenolic printed circuit board having 1 oz. Copper ribbon .080" wide. The distance from the bottom of the reflector cup to the top of the PCB was 0.3". The LED leads were nickel-iron Alloy 42.

Fig. 9 Pulse Derating Curve



Package Outlines (Dimensions in mm, unless otherwise specified)



Cathode mark: Short solder lead